BC856BWT1, SBC856BWT1 Series, BC857BWT1, SBC857BWT1 Series, BC858AWT1 Series

General Purpose Transistors

PNP Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC−70/SOT−323 which is designed for low power surface mount applications.

Features

- AEC−Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC856, SBC856 BC857, SBC857 BC858	V_{CEO}	 −65 −45 −30	V
Collector-Base Voltage BC856, SBC856 BC857, SBC857 BC858	V_{CBO}	 −80 −50 −30	V
Emitter−Base Voltage	V_{EBO}	−5.0	V
Collector Current − Continuous	I_C	−100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) T_A = 25°C	P_D	150	mW
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	883	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR−5 = 1.0 x 0.75 x 0.062 in.

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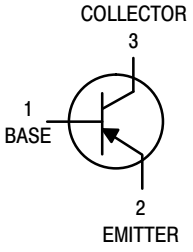
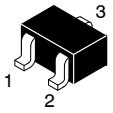
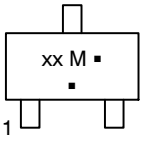
http://onsemi.com





SC−70/SOT−323
CASE 419
STYLE 3

MARKING DIAGRAM



xx = Specific Device Code
M = Date Code*
▪ = Pb−Free Package
(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I_C = −10 mA)	BC856, SBC856 Series BC857, SBC857 Series BC858 Series	$V_{(BR)CEO}$	−65 −45 −30	– – –	– – –	V
Collector – Emitter Breakdown Voltage (I_C = −10 μA, V_{EB} = 0)	BC856, SBC856 Series BC857B, SBC857B Only BC858 Series	$V_{(BR)CES}$	−80 −50 −30	– – –	– – –	V
Collector – Base Breakdown Voltage (I_C = −10 μA)	BC856, SBC856 Series BC857, SBC857 Series BC858 Series	$V_{(BR)CBO}$	−80 −50 −30	– – –	– – –	V
Emitter – Base Breakdown Voltage (I_E = −1.0 μA)	BC856, SBC856 Series BC857, SBC857 Series BC858 Series	$V_{(BR)EBO}$	−5.0 −5.0 −5.0	– – –	– – –	V
Collector Cutoff Current (V_{CB} = −30 V) (V_{CB} = −30 V, T_A = 150°C)		I_{CBO}	– –	– –	−15 −4.0	nA μA
ON CHARACTERISTICS						
DC Current Gain (I_C = −10 μA, V_{CE} = −5.0 V) SBC857B BC858B	BC856A, BC585A BC856B, SBC856B, BC857B,	h_{FE}	– –	90 150	– –	–
	BC857C		–	270	–	
(I_C = −2.0 mA, V_{CE} = −5.0 V) SBC857B, BC858B	BC856A, BC858A BC856B, SBC856B, BC857B,		125 220	180 290	250 475	
	BC857C		420	520	800	
Collector – Emitter Saturation Voltage (I_C = −10 mA, I_B = −0.5 mA) (I_C = −100 mA, I_B = −5.0 mA)		$V_{CE(sat)}$	 – –	 – –	 −0.3 −0.65	V
Base – Emitter Saturation Voltage (I_C = −10 mA, I_B = −0.5 mA) (I_C = −100 mA, I_B = −5.0 mA)		$V_{BE(sat)}$	 – –	 −0.7 −0.9	 – –	V
Base – Emitter On Voltage (I_C = −2.0 mA, V_{CE} = −5.0 V) (I_C = −10 mA, V_{CE} = −5.0 V)		$V_{BE(on)}$	 −0.6 –	 – –	 −0.75 −0.82	V
SMALL−SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product (I_C = −10 mA, V_{CE} = −5.0 Vdc, f = 100 MHz)		f_T	100	–	–	MHz
Output Capacitance (V_{CB} = −10 V, f = 1.0 MHz)		C_{ob}	–	–	4.5	pF
Noise Figure (I_C = −0.2 mA, V_{CE} = −5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		NF	–	–	10	dB

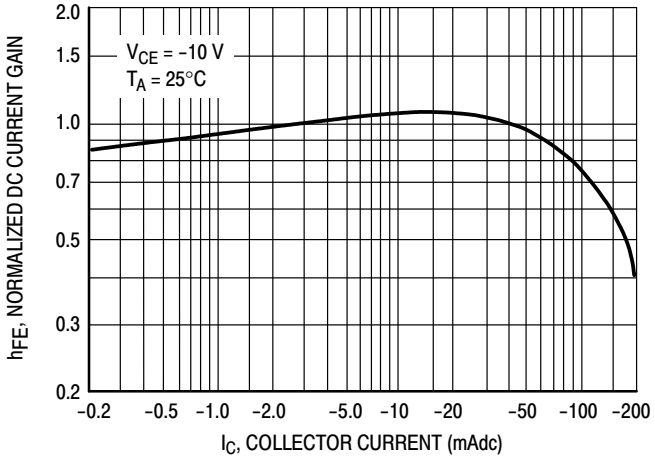


Figure 1. Normalized DC Current Gain

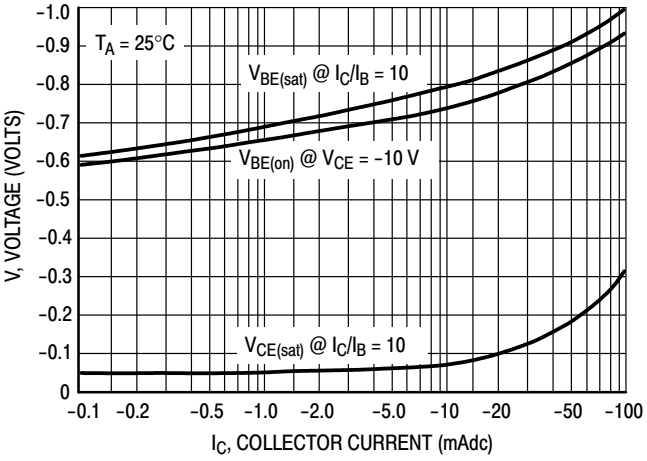


Figure 2. “Saturation” and “On” Voltages

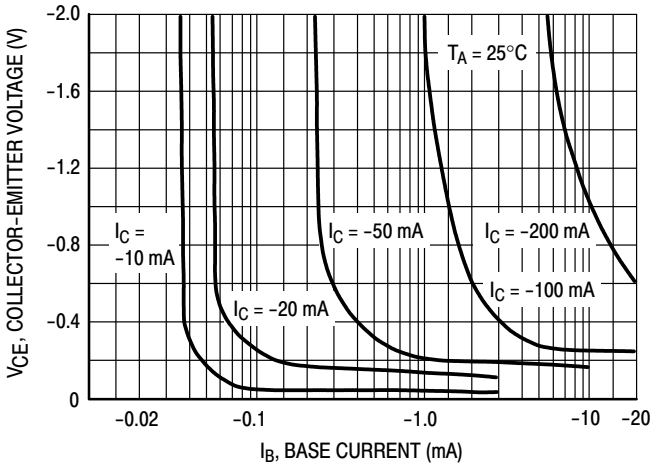


Figure 3. Collector Saturation Region

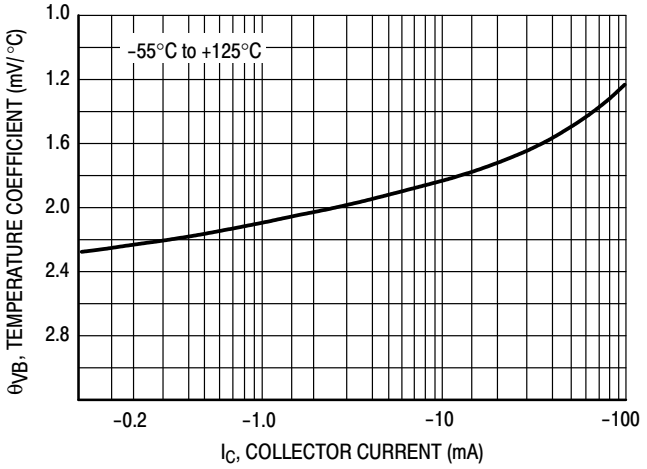


Figure 4. Base−Emitter Temperature Coefficient

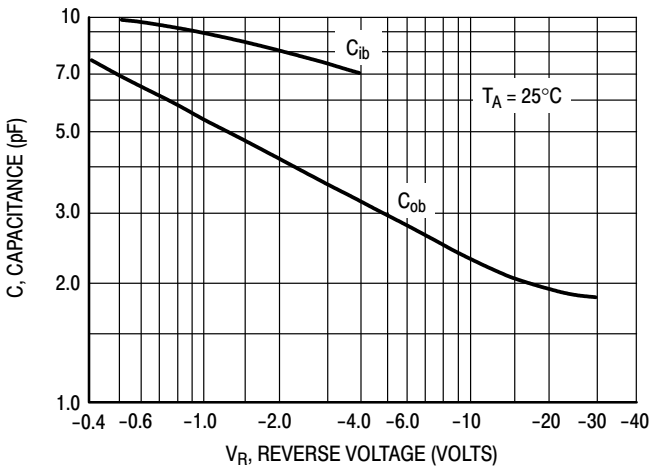


Figure 5. Capacitances

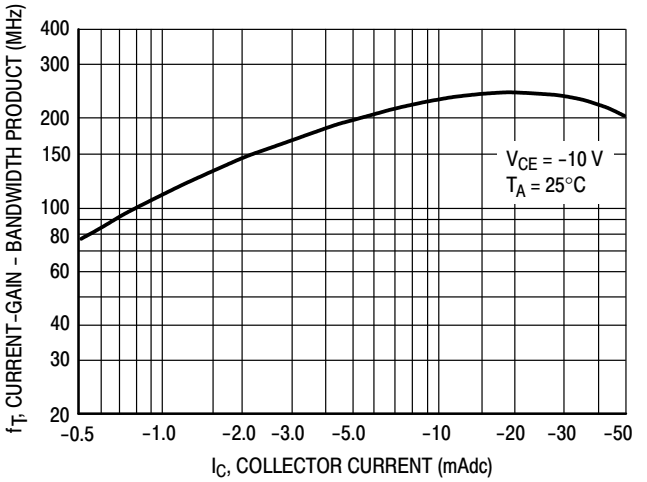


Figure 6. Current−Gain − Bandwidth Product

BC856/SBC856

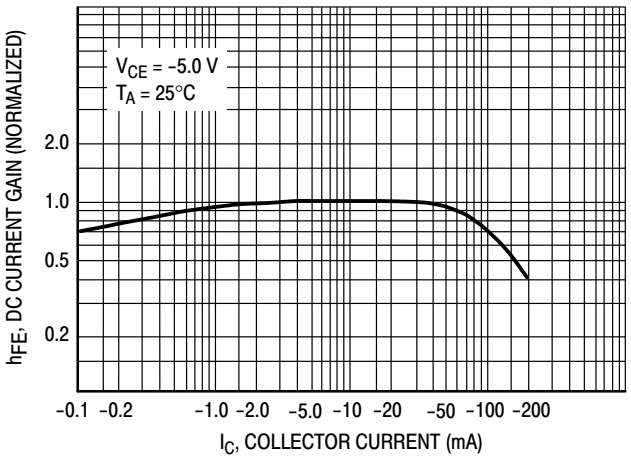


Figure 7. DC Current Gain

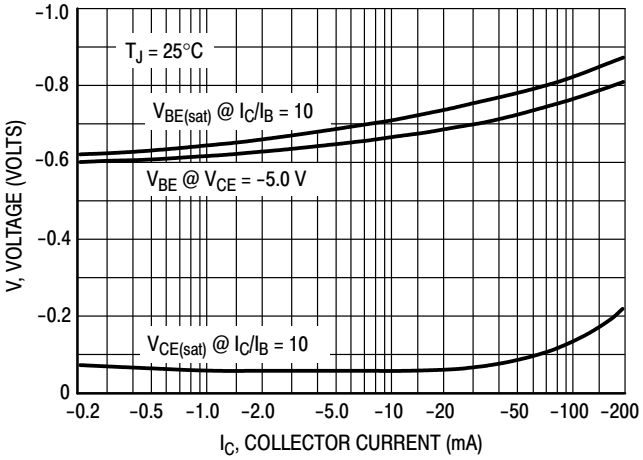


Figure 8. “On” Voltage

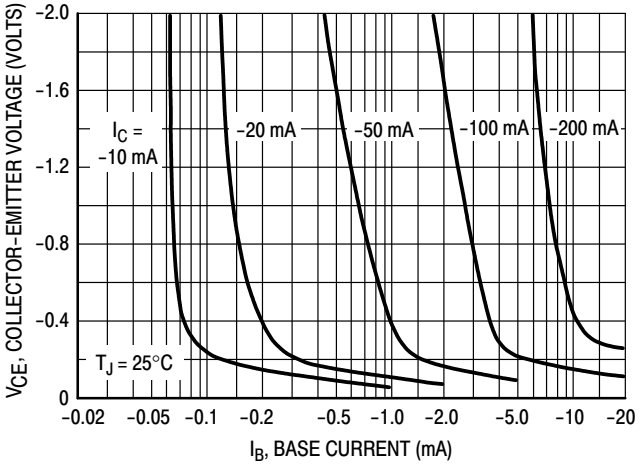


Figure 9. Collector Saturation Region

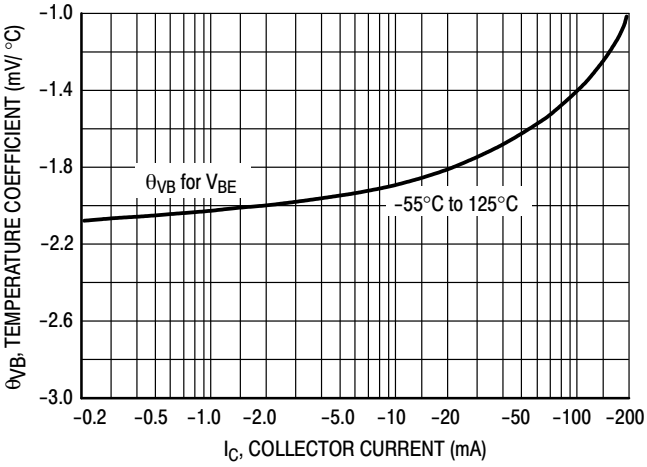


Figure 10. Base−Emitter Temperature Coefficient

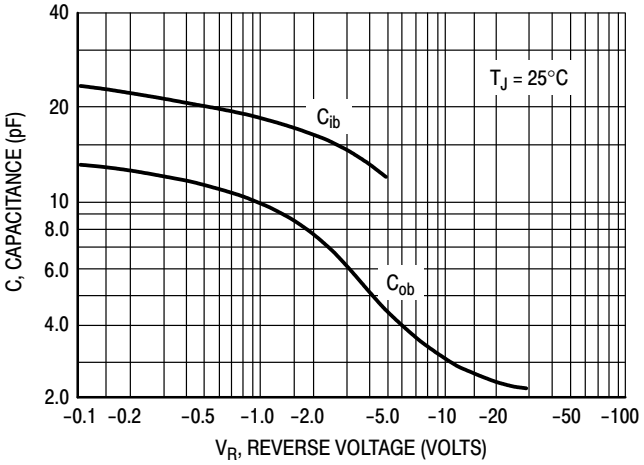


Figure 11. Capacitance

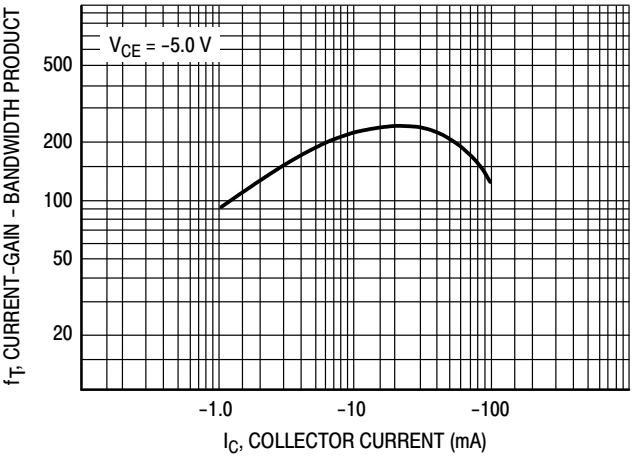


Figure 12. Current−Gain − Bandwidth Product

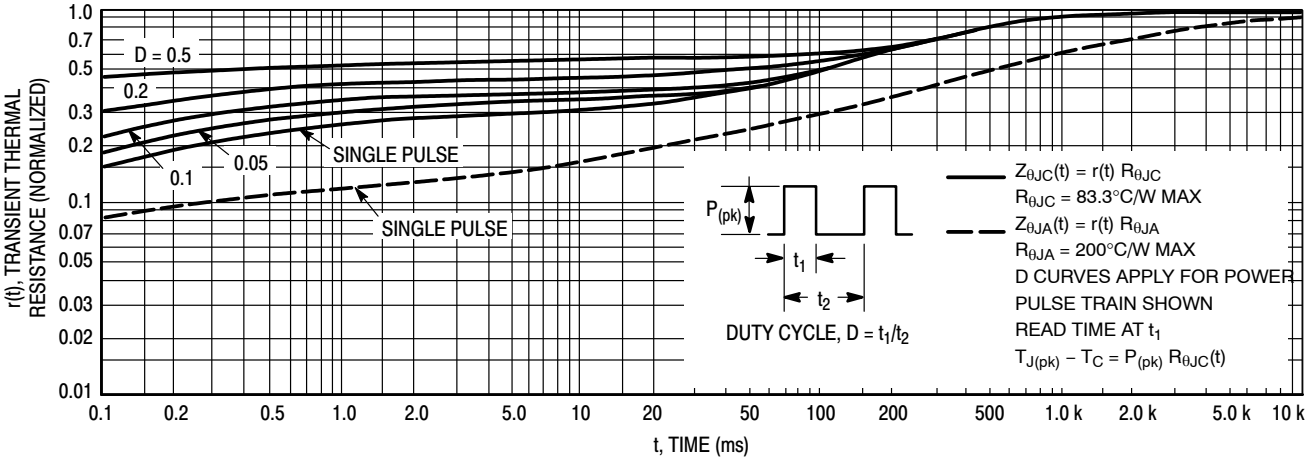


Figure 13. Thermal Response

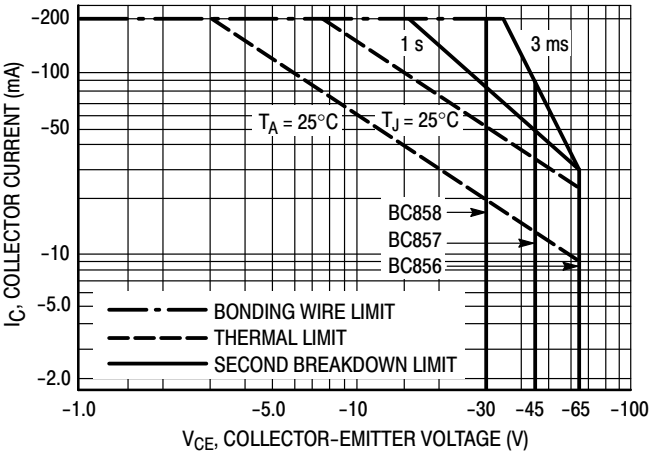


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C–V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)}$ = 150°C; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

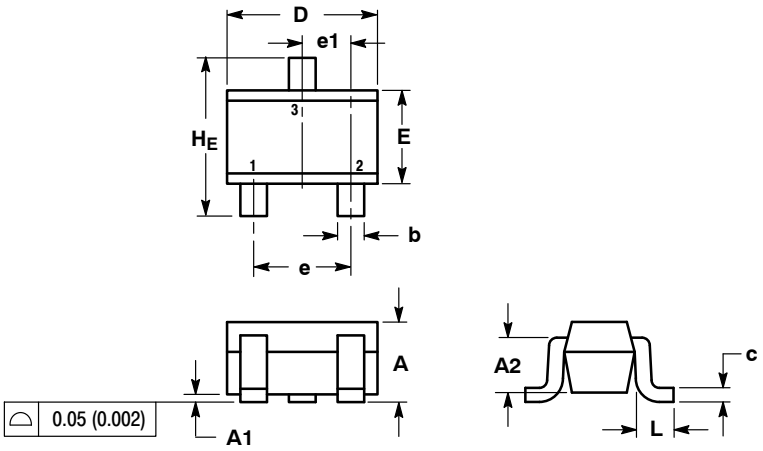
ORDERING INFORMATION

Device	Marking	Package	Shipping†
BC856BWT1G	3B	SC–70/SOT–323 (Pb–Free)	3,000 / Tape & Reel
SBC856BWT1G			
BC857BWT1G	3F	SC–70/SOT–323 (Pb–Free)	3,000 / Tape & Reel
SBC857BWT1G			
BC857CWT1G	3G	SC–70/SOT–323 (Pb–Free)	3,000 / Tape & Reel
BC858AWT1G	3J	SC–70/SOT–323 (Pb–Free)	3,000 / Tape & Reel
BC858BWT1G	3K	SC–70/SOT–323 (Pb–Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC−70 (SOT−323)
CASE 419−04
ISSUE N

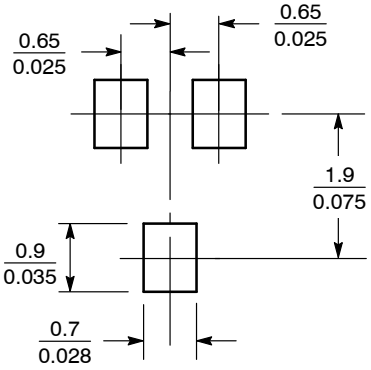


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

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